

IGBT-Wechselrichter/IGBT-inverter

Höchstzulässige Werte/maximum rated values

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C\ nom}$ I_C	100 200	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_P = 1\ \text{ms}, T_C = 80^{\circ}\text{C}$	I_{CRM}	200	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	P_{tot}	780	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte/characteristic values

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 100\ \text{A}, V_{GE} = 15\ \text{V}, T_{vj} = 25^{\circ}\text{C}$ $I_C = 100\ \text{A}, V_{GE} = 15\ \text{V}, T_{vj} = 125^{\circ}\text{C}$	$V_{CE\ sat}$		2,10 2,40	2,60 2,90	V V
Gate-Schwellenspannung gate threshold voltage	$I_C = 4,00\ \text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	4,5	5,5	6,5	V
Gateladung gate charge	$V_{GE} = -15\ \text{V} \dots +15\ \text{V}$	Q_G		1,10		μC
Interner Gatewiderstand internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}		2,5		Ω
Eingangskapazität input capacitance	$f = 1\ \text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\ \text{V}, V_{GE} = 0\ \text{V}$	C_{ies}		6,50		nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\ \text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\ \text{V}, V_{GE} = 0\ \text{V}$	C_{res}		0,42		nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1200\ \text{V}, V_{GE} = 0\ \text{V}, T_{vj} = 25^{\circ}\text{C}$	I_{CES}			5,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\ \text{V}, V_{GE} = 20\ \text{V}, T_{vj} = 25^{\circ}\text{C}$	I_{GES}			400	nA
Einschaltverzögerungszeit (ind. Last) turn-on delay time (inductive load)	$I_C = 100\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 6,8\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 6,8\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$t_{d\ on}$		0,06 0,06		μs μs
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 100\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 6,8\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 6,8\ \Omega, T_{vj} = 125^{\circ}\text{C}$	t_r		0,05 0,05		μs μs
Abschaltverzögerungszeit (ind. Last) turn-off delay time (inductive load)	$I_C = 100\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6,8\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6,8\ \Omega, T_{vj} = 125^{\circ}\text{C}$	$t_{d\ off}$		0,35 0,40		μs μs
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 100\ \text{A}, V_{CE} = 600\ \text{V}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6,8\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6,8\ \Omega, T_{vj} = 125^{\circ}\text{C}$	t_f		0,06 0,08		μs μs
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 100\ \text{A}, V_{CE} = 600\ \text{V}, L_S = 60\ \text{nH}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 6,8\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Gon} = 6,8\ \Omega, T_{vj} = 125^{\circ}\text{C}$	E_{on}		10,0		mJ mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 100\ \text{A}, V_{CE} = 600\ \text{V}, L_S = 60\ \text{nH}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6,8\ \Omega, T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6,8\ \Omega, T_{vj} = 125^{\circ}\text{C}$	E_{off}		12,0		mJ mJ
Kurzschlußverhalten SC data	$t_P \leq 10\ \mu\text{s}, V_{GE} \leq 15\ \text{V}$ $T_{vj} \leq 125^{\circ}\text{C}, V_{CC} = 900\ \text{V}, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	I_{SC}		650		A
Innerer Wärmewiderstand thermal resistance, junction to case	pro IGBT per IGBT	R_{thJC}			0,16	K/W

prepared by: Mark Münzer	date of publication: 2003-5-21
approved by: Wilhelm Rusche	revision: 3.1

Diode-Wechselrichter/diode-inverter
Höchstzulässige Werte/maximum rated values

Periodische Spitzensperrspannung repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom DC forward current		I_F	100	A
Periodischer Spitzenstrom repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	200	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	1700	A^2s

Charakteristische Werte/characteristic values

			min.	typ.	max.	
Durchlassspannung forward voltage	$I_F = 100\text{ A}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $I_F = 100\text{ A}, V_{GE} = 0\text{ V}, T_{vj} = 125^{\circ}\text{C}$	V_F		1,80 1,70	2,30 2,20	V V
Rückstromspitze peak reverse recovery current	$I_F = 100\text{ A}, -di_F/dt = 2700\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 125^{\circ}\text{C}$	I_{RM}		125 155		A A
Sperrverzögerungsladung recovered charge	$I_F = 100\text{ A}, -di_F/dt = 2700\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 125^{\circ}\text{C}$	Q_r		12,0 22,0		μC μC
Abschaltenergie pro Puls reverse recovery energy	$I_F = 100\text{ A}, -di_F/dt = 2700\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 600\text{ V}, V_{GE} = -15\text{ V}, T_{vj} = 125^{\circ}\text{C}$	E_{rec}		4,00 9,00		mJ mJ
Innerer Wärmewiderstand thermal resistance, junction to case	pro Diode per diode	R_{thJC}			0,30	K/W

prepared by: Mark Münzer	date of publication: 2003-5-21
approved by: Wilhelm Rusche	revision: 3.1

Modul/module

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISO}	2,5		kV
Material Modulgrundplatte material of module baseplate			Cu		
Material für innere Isolation material for internal insulation			Al ₂ O ₃		
Kriechstrecke creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		20,0		mm
Luftstrecke clearance distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		11,0		mm
Vergleichszahl der Kriechwegbildung comparative tracking index		CTI	> 425		
			min.	typ.	max.
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	R _{thCH}		0,01	K/W
Modulinduktivität stray inductance module		L _{sCE}		20	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	T _C = 25°C, pro Zweig / per arm	R _{CC'+EE'}		0,70	mΩ
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T _{vj max}			150 °C
Temperatur im Schaltbetrieb temperature under switching conditions		T _{vj op}	-40		125 °C
Lagertemperatur storage temperature		T _{stg}	-40		125 °C
Anzugsdrehmoment f. mech. Befestigung mounting torque	Schraube / screw M6	M	3,00	-	6,00 Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	Schraube / screw M6	M	2,5	-	5,0 Nm
Gewicht weight		G		340	g

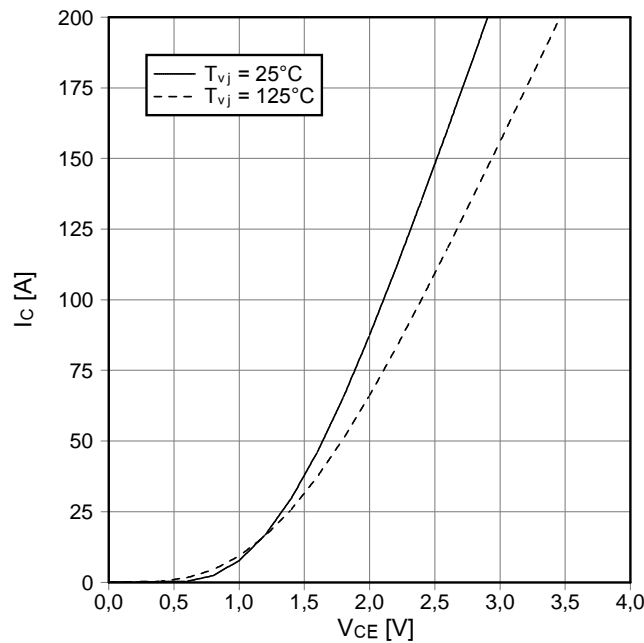
Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.

This technical information specifies semiconductor devices but guarantees no characteristics. It is valid with the appropriate technical explanations.

prepared by: Mark Münzer	date of publication: 2003-5-21
approved by: Wilhelm Rusche	revision: 3.1

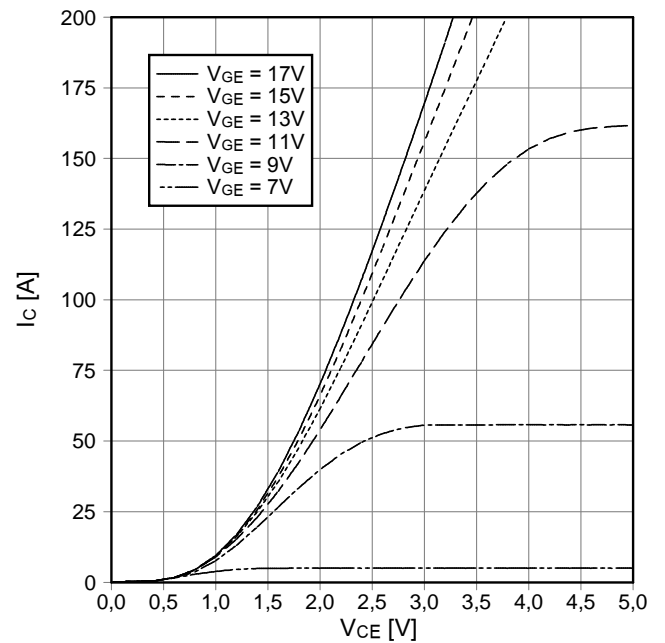
Ausgangskennlinie IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)

$I_c = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



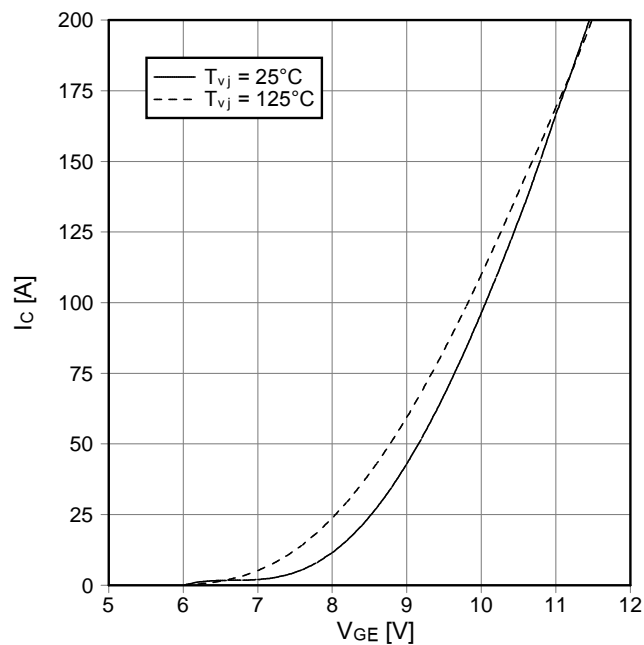
Ausgangskennlinienfeld IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)

$I_c = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



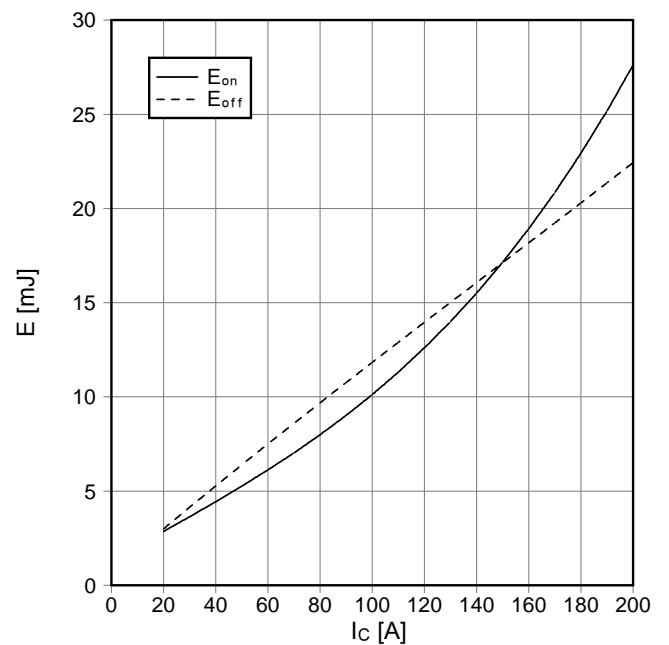
Übertragungscharakteristik IGBT-Wechselr. (typisch)
transfer characteristic IGBT-inverter (typical)

$I_c = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



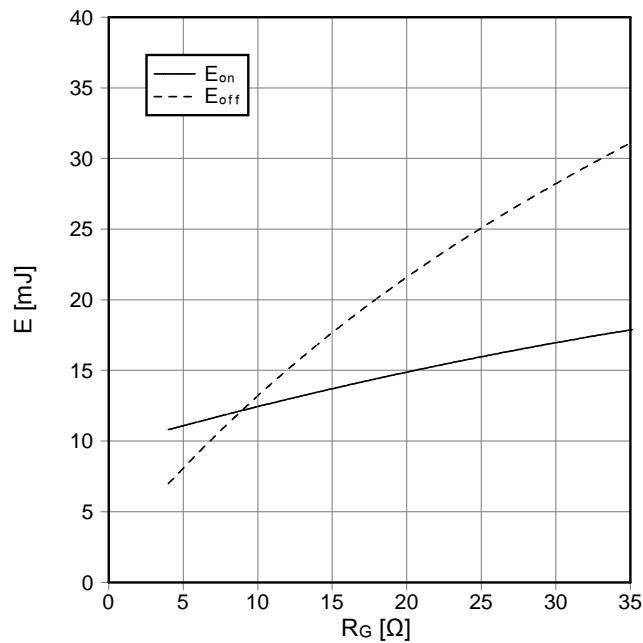
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-inverter (typical)

$E_{on} = f(I_c)$, $E_{off} = f(I_c)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $R_{Goff} = 6,8\ \Omega$, $V_{CE} = 600\text{ V}$,
 $T_{vj} = 125^\circ\text{C}$

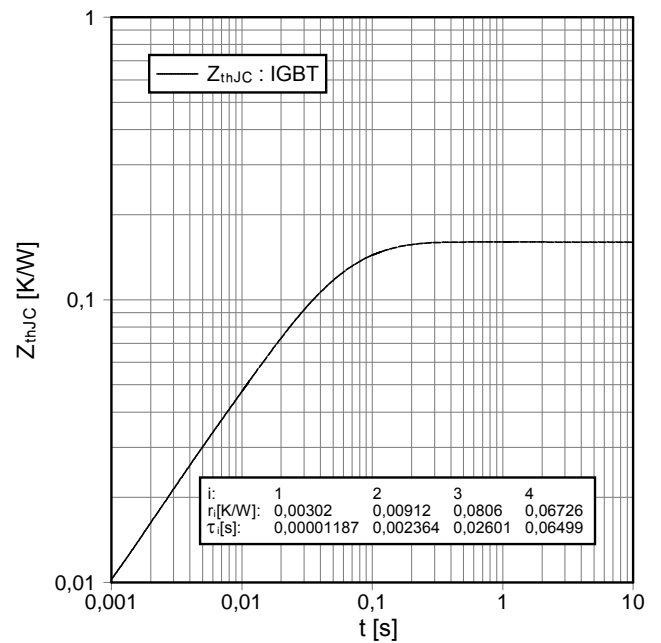


prepared by: Mark Münzer	date of publication: 2003-5-21
approved by: Wilhelm Rusche	revision: 3.1

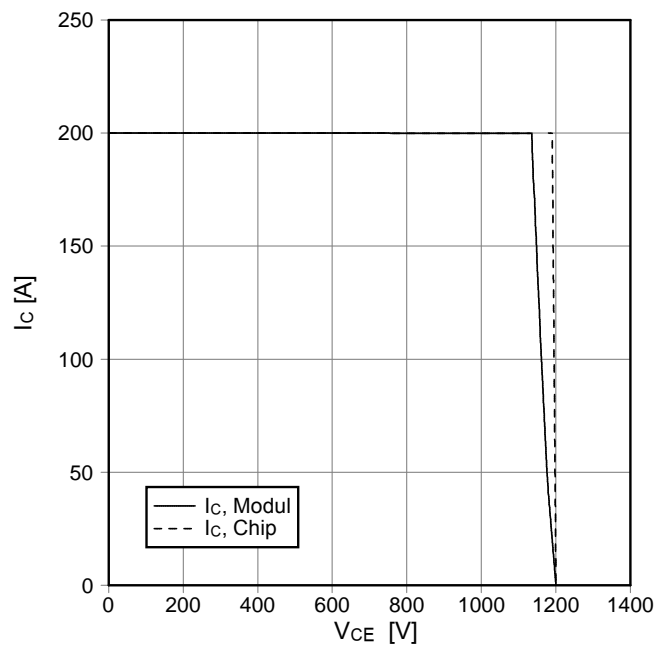
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-Inverter (typical)
 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_c = 100\text{ A}$, $V_{CE} = 600\text{ V}$, $T_{vj} = 125^\circ\text{C}$



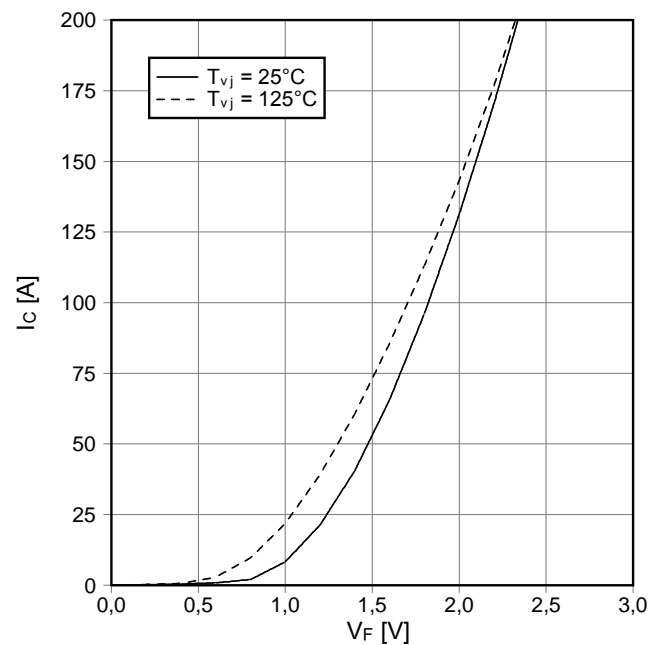
Transienter Wärmewiderstand IGBT-Wechselr.
transient thermal impedance IGBT-inverter
 $Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)
reverse bias safe operating area IGBT-inv. (RBSOA)
 $I_c = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6,8\ \Omega$, $T_{vj} = 125^\circ\text{C}$



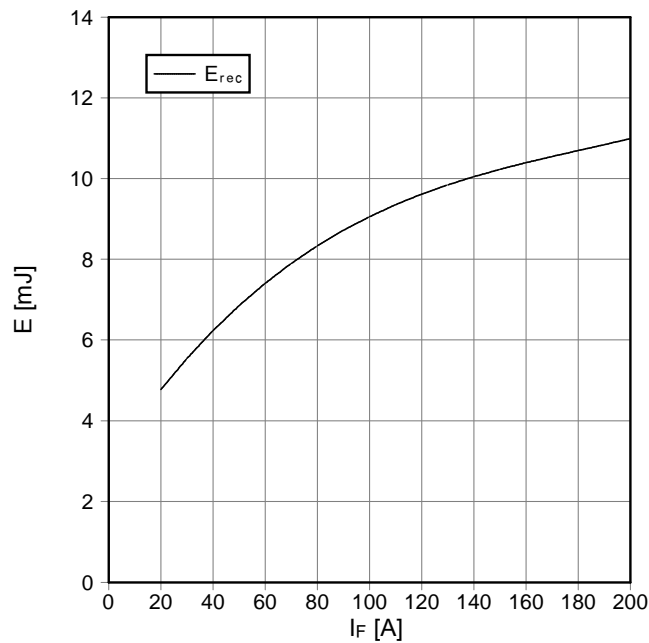
Durchlaßkennlinie der Diode-Wechselr. (typisch)
forward characteristic of diode-inverter (typical)
 $I_F = f(V_F)$



prepared by: Mark Münzer	date of publication: 2003-5-21
approved by: Wilhelm Rusche	revision: 3.1

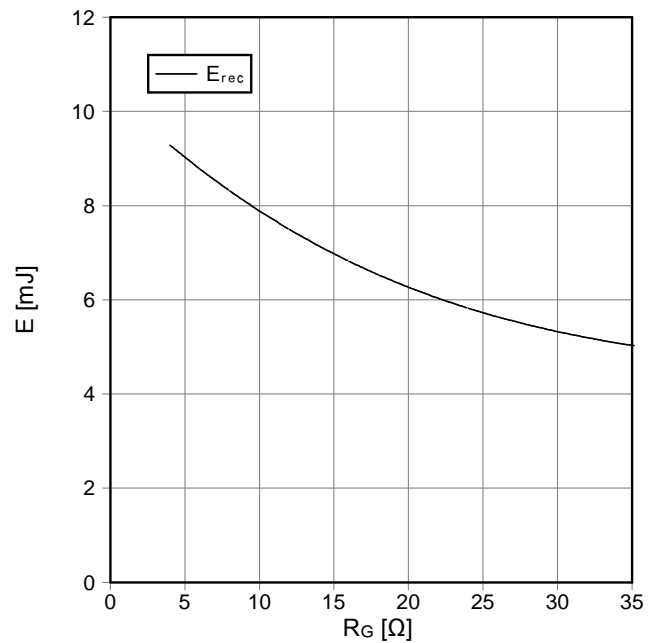
Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 6,8 \Omega$, $V_{CE} = 600 V$, $T_{vj} = 125^\circ C$



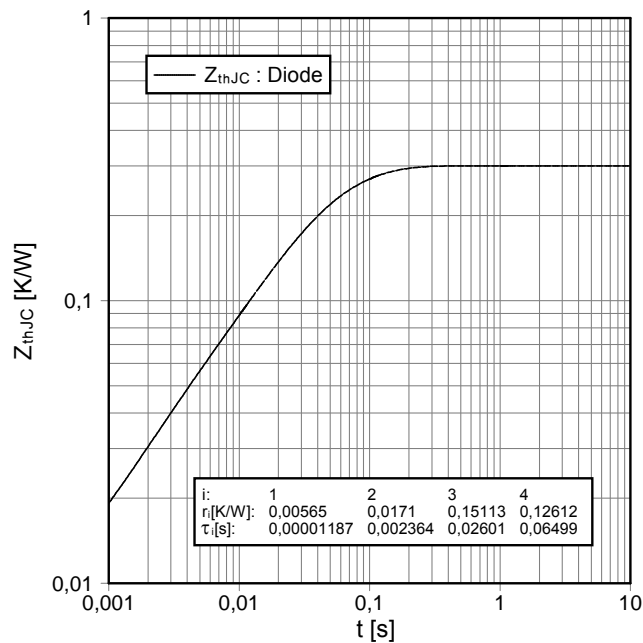
Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 100 A$, $V_{CE} = 600 V$, $T_{vj} = 125^\circ C$



Transienter Wärmewiderstand Diode-Wechselr.
transient thermal impedance diode-inverter

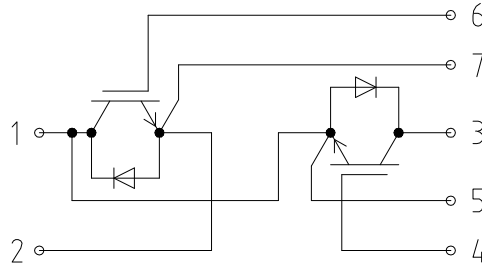
$Z_{thJC} = f(t)$



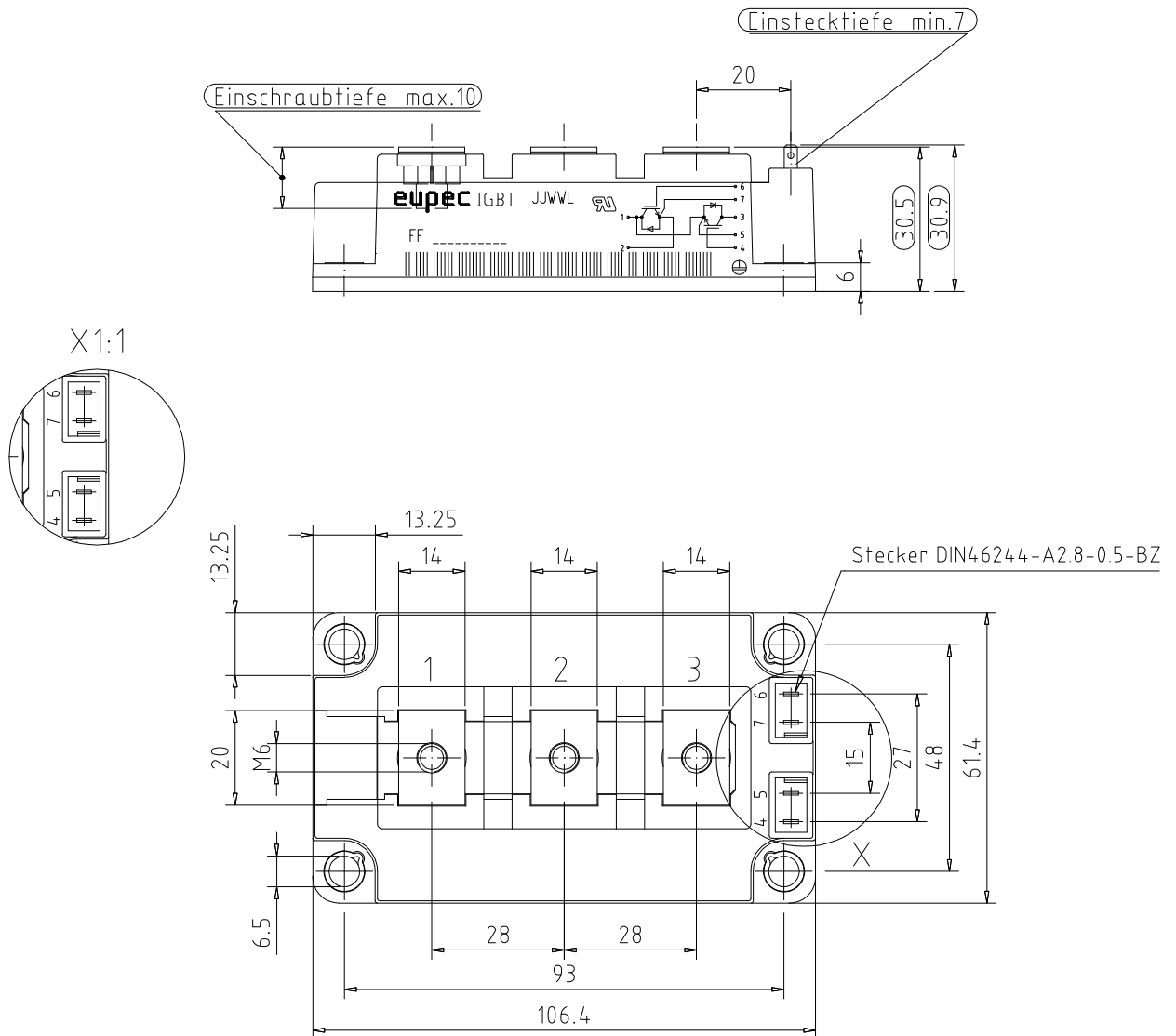
i:	1	2	3	4
r_i [K/W]:	0,00565	0,0171	0,15113	0,12612
τ_i [s]:	0,00001187	0,002364	0,02601	0,06499

prepared by: Mark Münzer	date of publication: 2003-5-21
approved by: Wilhelm Rusche	revision: 3.1

Schaltplan/circuit diagram



Gehäuseabmessungen/package outlines



prepared by: Mark Münzer	date of publication: 2003-5-21
approved by: Wilhelm Rusche	revision: 3.1

Terms & Conditions of Usage

Attention

The present product data is exclusively subscribed to technically experienced staff. This Data Sheet is describing the specification of the products for which a warranty is granted exclusively pursuant the terms and conditions of the supply agreement. There will be no guarantee of any kind for the product and its specifications. Changes to the Data Sheet are reserved.

You and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application. Should you require product information in excess of the data given in the Data Sheet, please contact your local Sales Office via "www.eupec.com / sales & contact".

Warning

Due to technical requirements the products may contain dangerous substances. For information on the types in question please contact your local Sales Office via "www.eupec.com / sales & contact".